

iscN-Channel MOSFET Transistor**TK5A55D, ITK5A55D****• FEATURES**

- Low drain-source on-resistance:
 $R_{DS(ON)} = 1.4\Omega$ (typ.)
- Enhancement mode:
 $V_{th} = 2.4$ to $4.4V$ ($V_{DS} = 10V$, $I_D = 1.0mA$)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• DESCRIPTION

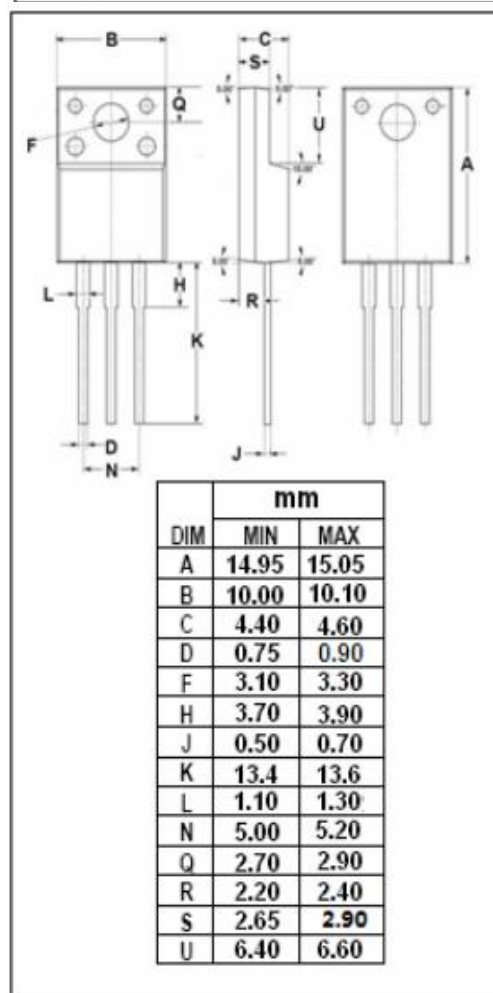
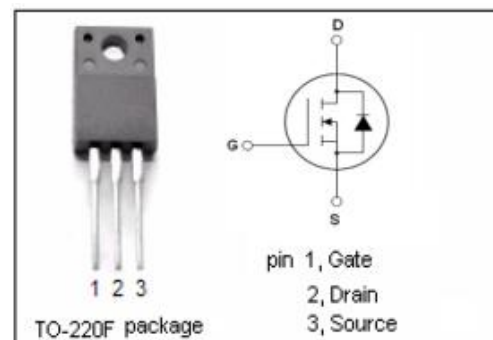
- Switching Voltage Regulators

• ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DS}	Drain-Source Voltage	550	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-Continuous	5	A
I_{DM}	Drain Current-Single Pulsed	20	A
P_D	Total Dissipation @ $T_c = 25^\circ C$	35	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature	-55~150	$^\circ C$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(ch-c)}$	Channel-to-case thermal resistance	3.57	$^\circ C/W$
$R_{th(ch-a)}$	Channel-to-ambient thermal resistance	62.5	$^\circ C/W$



iscN-Channel MOSFET Transistor**TK5A55D, ITK5A55D****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V; I_D=10mA$	550			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=10V; I_D=1.0mA$	2.4		4.4	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V; I_D=2.5A$		1400	1700	$m\Omega$
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 30V; V_{DS}=0V$			± 1	μA
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=550V; V_{GS}=0V$			10	μA
V_{SDF}	Diode forward voltage	$I_{DR}=5A, V_{GS}=0V$			1.7	V

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